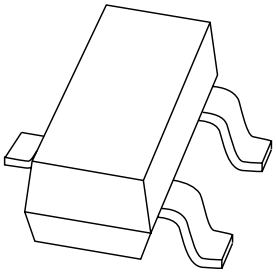
DATA SHEET



BSR13; BSR14
NPN switching transistors

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 13

NPN switching transistors BSR13; BSR14

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear applications.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.
PNP complements: BSR15 and BSR16.

MARKING

TYPE NUMBER	MARKING CODE(1)
BSR13	U7*
BSR14	U8*

Note

1. * = p : Made in Hong Kong.
   * = t : Made in Malaysia.
   * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

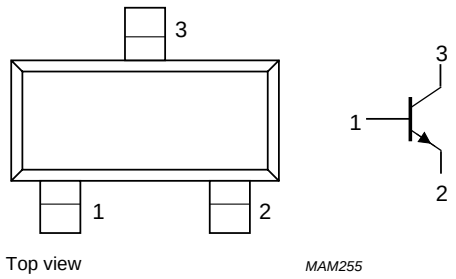


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSR13	–	plastic surface mounted package; 3 leads	SOT23
BSR14			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BSR13		–	60	V
	BSR14		–	75	V
V_{CEO}	collector-emitter voltage	open base			
	BSR13		–	30	V
	BSR14		–	40	V
V_{EBO}	emitter-base voltage	open collector			
	BSR13		–	5	V
	BSR14		–	6	V
I_C	collector current (DC)		–	800	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

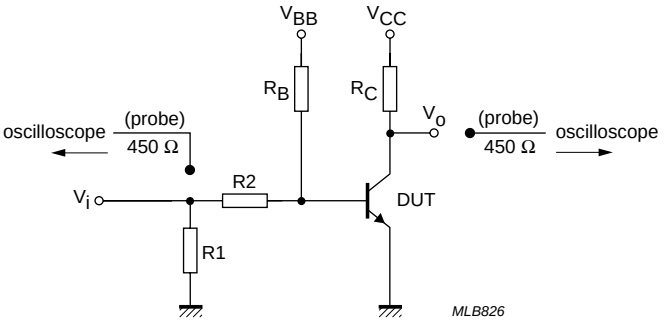
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current				
	BSR13	$I_E = 0$; $V_{CB} = 50$ V	–	30	nA
		$I_E = 0$; $V_{CB} = 50$ V; $T_j = 150$ °C	–	10	μA
	collector cut-off current				
	BSR14	$I_E = 0$; $V_{CB} = 60$ V	–	10	nA
		$I_E = 0$; $V_{CB} = 60$ V; $T_j = 150$ °C	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5$ V			
	BSR13		–	30	nA
	BSR14		–	10	nA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
h_{FE}	DC current gain	I_C = 0.1 mA; V_{CE} = 10 V; note 1	35	–	
		I_C = 1 mA; V_{CE} = 10 V; note 1	50	–	
		I_C = 10 mA; V_{CE} = 10 V; note 1	75	–	
		I_C = 150 mA; V_{CE} = 10 V; note 1	100	300	
		I_C = 150 mA; V_{CE} = 1 V; note 1	50	–	
	DC current gain	I_C = 500 mA; V_{CE} = 10 V; note 1			
	BSR13		30	–	
	BSR14		40	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA			
	BSR13		–	400	mV
	BSR14		–	300	mV
	collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA			
	BSR13		–	1.6	V
	BSR14		–	1	V
V_{BEsat}	base-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA			
	BSR13		–	1.3	V
	BSR14		0.6	1.2	V
	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA			
	BSR13		–	2.6	V
	BSR14		–	2	V
C_c	collector capacitance	$I_E = I_e$ = 0; V_{CB} = 10 V; f = 1 MHz	–	8	pF
f_T	transition frequency	I_C = 20 mA; V_{CE} = 20 V; f = 100 MHz			
	BSR13		250	–	MHz
	BSR14		300	–	MHz
Switching times (between 10% and 90% levels); see Fig.2					
t_{on}	turn-on time	I_{Con} = 150 mA; I_{Bon} = 15 mA; I_{Boff} = −15 mA	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

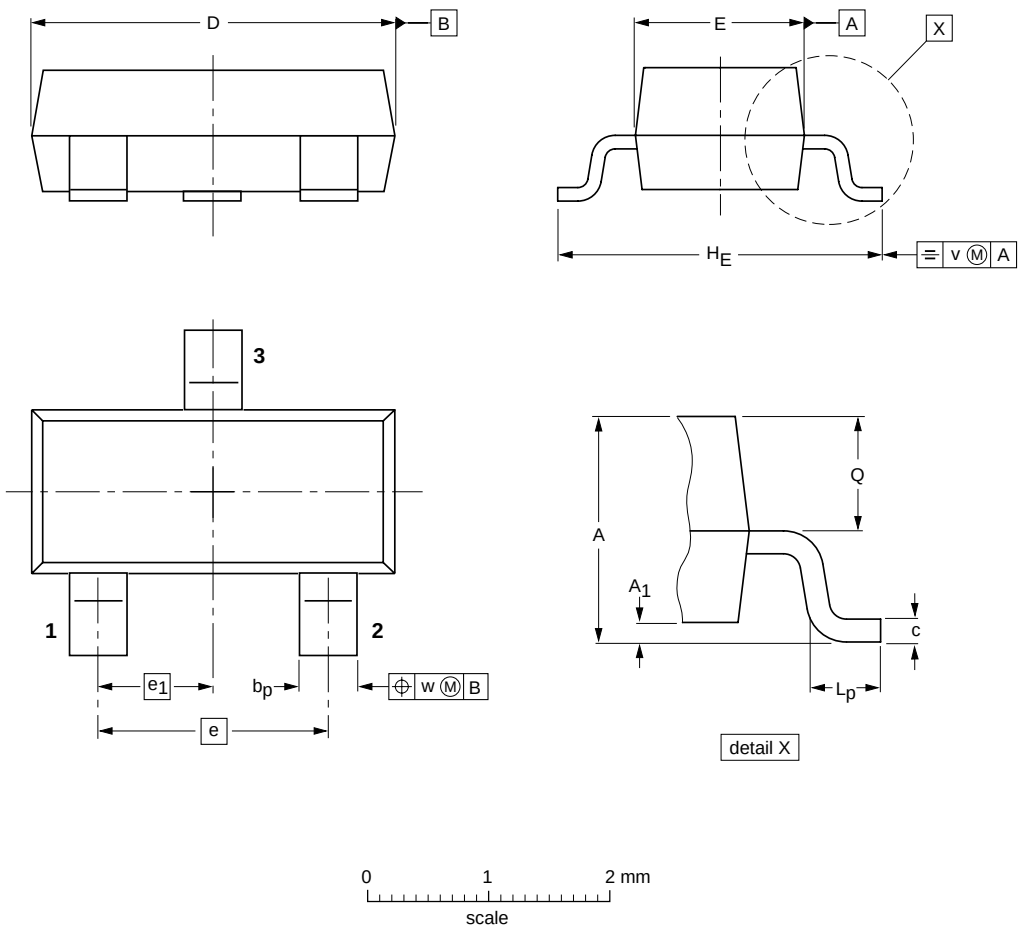


V_i = 9.5 V; T = 500 μs; t_p = 10 μs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = −3.5 V; V_{CC} = 29.5 V.
Oscilloscope: input impedance $Z_i = \geq 100$ Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				~~04-11-04~~ 06-03-16